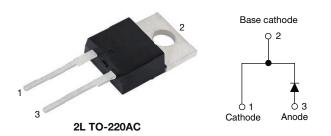
**Vishay Semiconductors** 

FREE

Hyperfast Rectifier, 30 A FRED Pt<sup>®</sup> G5



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## LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS						
I <sub>F(AV)</sub> 30 A						
V <sub>R</sub>	1200 V					
V <sub>F</sub> at I <sub>F</sub> at 125 °C	1.7 V					
t <sub>rr</sub>	32 ns					
T <sub>J</sub> max.	175 °C					
Package	2L TO-220AC					
Circuit configuration	Single					

### FEATURES

- Hyperfast and optimized Qrr
- Best in class forward voltage drop and switching RoHS
  losses trade off
  HALOGEN
- Optimized for high speed operation
- 175 °C maximum operating junction temperature
- · Polyimide passivation
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

## **DESCRIPTION / APPLICATIONS**

Featuring a unique combination of low conduction and switching losses, this rectifier is the right choice for high frequency converters, both soft switched / resonant.

Specifically designed to improve efficiency of PFC and output rectification stages of EV / HEV battery charging stations, booster stage of solar inverters and UPS applications, these devices are perfectly matched to operate with MOSFETs or high speed IGBTs.

## **MECHANICAL DATA**

Case: 2L TO-220AC

Molding compound meets UL 94 V-0 flammability rating

**Terminals:** matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

Polarity: as per marking device details

ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Repetitive peak reverse voltage	V <sub>RRM</sub>		1200	V				
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 96 °C, D = 0.50	30					
Non-repetitive peak surge current	I <sub>FSM</sub>	$T_{C}$ = 96 °C, $t_{p}$ = 10 ms, sine wave	240	А				
Repetitive peak forward current	I <sub>FRM</sub>	T <sub>C</sub> = 45 °C, D = 0.50, f = 20 kHz	60					
Operating junction and storage temperature	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C				

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	SYMBOL TEST CONDITIONS MIN. TYP. I				UNITS		
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μA	1200	-	-			
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 30 A	-	1.9	2.5	V		
		I <sub>F</sub> = 30 A, T <sub>J</sub> = 125 °C	-	1.7	-			
	I <sub>R</sub>	V <sub>R</sub> = V <sub>R</sub> rated	-	-	50			
Reverse leakage current		$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	500	μA		
Junction capacitance	CT	V <sub>R</sub> = 200 V	-	17	-	pF		
Series inductance	L <sub>S</sub>	Measured to lead 5 mm from package body	-	8	-	nH		

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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25 \text{ °C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
		I <sub>F</sub> = 1.0 A, dI <sub>F</sub> /dt =	100 A/ $\mu$ s, V <sub>R</sub> = 30 V	-	32	58	
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	113	-	ns
		T <sub>J</sub> = 125 °C		-	175	-	
Peak recovery current	1	T <sub>J</sub> = 25 °C	I <sub>F</sub> = 20 A dI <sub>F</sub> /dt = 600 A/µs	-	17	-	A
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C	$V_{\rm R} = 400 \text{ V}$	-	24	-	
	0	T <sub>J</sub> = 25 °C		-	850	-	nC
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	2150	-	
	+	T <sub>J</sub> = 25 °C		-	85	-	20
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	132	-	ns
Poak racevany ourrent		T <sub>J</sub> = 25 °C	I <sub>F</sub> = 30 A dI <sub>F</sub> /dt = 1000 A/μs V <sub>R</sub> = 800 V	-	30	-	A
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C		-	43	-	
Reverse recovery charge	0	T <sub>J</sub> = 25 °C		-	1350	-	
	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	3215	-	nC

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Thermal resistance, junction-to-case	R <sub>thJC</sub>		-	-	1.1	°C/W		
Maiaht			-	2.0	-	g		
Weight			-	0.07	-	oz.		
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)		
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55	-	175	°C		
Marking device		Case style 2L TO-220AC	E5TH3012					

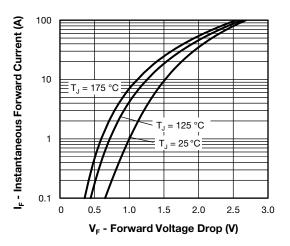


Fig. 1 - Typical Forward Voltage Drop Characteristics

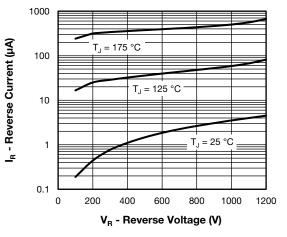
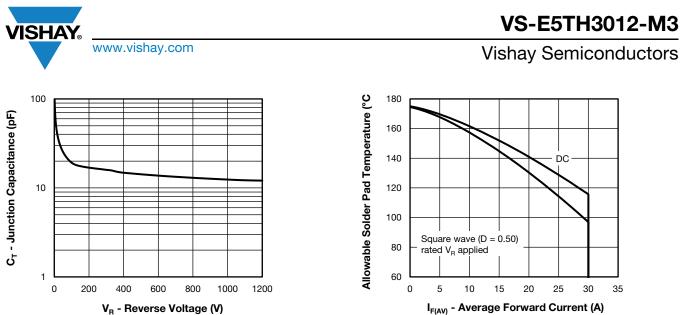


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

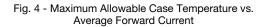
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V<sub>R</sub> - Reverse Voltage (V)

Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage



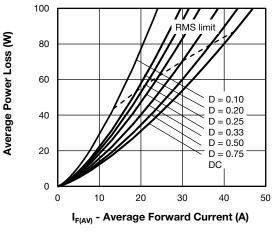


Fig. 5 - Forward Power Loss Characteristics

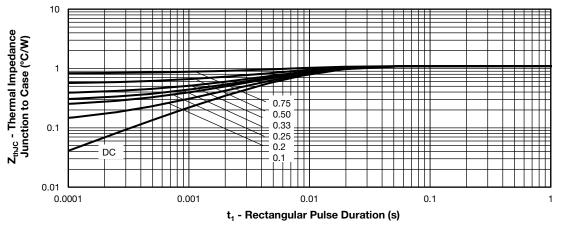


Fig. 6 - Thermal Impedance ZthJC Characteristics

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400

250

225

200

175

150

125

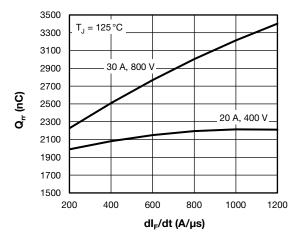
100

75

200

t<sub>rr</sub> (ns)

# T<sub>J</sub> = 125 °C



VS-E5TH3012-M3

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**dI<sub>F</sub>/dt (A/μs)** Fig. 7 - Typical Reverse Recovery Time vs. dI<sub>F</sub>/dt

800

1000

1200

600



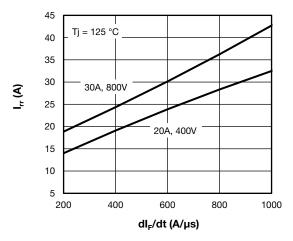


Fig. 9 - Typical Recovery Current vs. dl<sub>F</sub>/dt



## **Vishay Semiconductors**



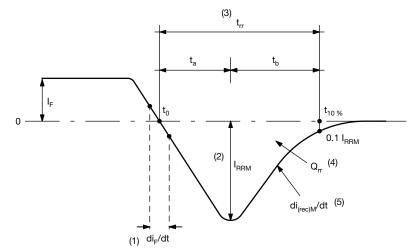


Fig. 10 - Reverse Recovery Waveform and Definitions

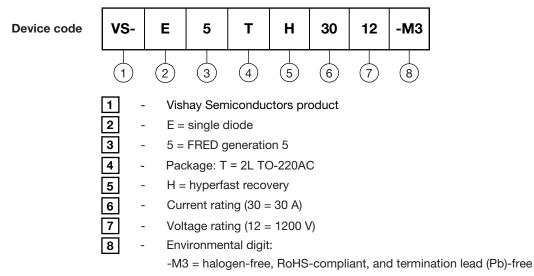
#### Notes

- <sup>(1)</sup> di<sub>F</sub>/dt rate of change of current through zero crossing
- <sup>(2)</sup> I<sub>RRM</sub> peak reverse recovery current
- <sup>(3)</sup>  $t_{rr}$  reverse recovery time measured from  $t_0$ , crossing point of negative going  $I_F$ , to point  $t_{10\%}$ , 0.1  $I_{RRM}$
- $^{(4)}~~Q_{rr}$  area under curve defined by  $t_0$  and  $t_{10~\%}$

$$Q_{rr} = \int_{t_0}^{t_{10\%}} I(t) dt$$

 $^{(5)}$  di<sub>(rec)</sub>M/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

#### **ORDERING INFORMATION TABLE**



ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-E5TH3012-M3	50	1000	Antistatic plastic tube				

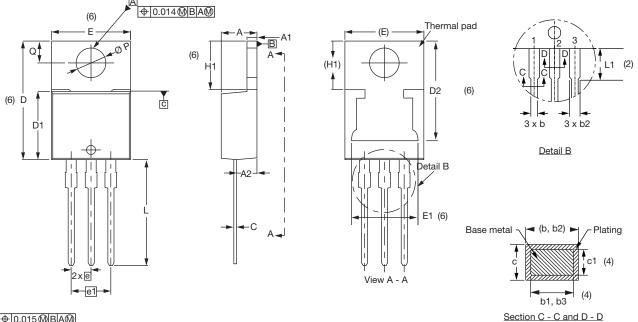
LINKS TO RELATED DOCUMENTS		
Dimensions	<u>w</u>	ww.vishay.com/doc?96154
Part marking information	<u>w</u>	ww.vishay.com/doc?95391
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# **3L TO-220AB**

#### **DIMENSIONS** in millimeters and inches



⊕0.015@BA@





SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STINDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.50	2.92	0.098	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.35	0.585	0.604	3
D1	8.38	9.02	0.330	0.355	

_		
Conforms to JEDEC <sup>®</sup>	outline	<b>TO-220AB</b>

SYMBOL	MILLIN	MILLIMETERS		INCHES		
STINDOL	MIN.	MAX.	MIN.	MAX.	NOTES	
D2	11.68	13.30	0.460	0.524	6, 7	
Ш	10.11	10.51	0.398	0.414	3, 6	
E1	6.86	8.89	0.270	0.350	6	
е	2.41	2.67	0.095	0.105		
e1	4.88	5.28	0.192	0.208		
H1	6.09	6.48	0.240	0.255	6	
L	13.52	14.02	0.532	0.552		
L1	3.32	3.82	0.131	0.150	2	
ØР	3.54	3.91	0.139	0.154		
Q	2.60	3.00	0.102	0.118		

#### Notes

<sup>(2)</sup> Lead dimension and finish uncontrolled in L1

- <sup>(4)</sup> Dimension b1, b3, and c1 apply to base metal only
- (5) Controlling dimensions: inches
- <sup>(6)</sup> Thermal pad contour optional within dimensions E, H1, D2, and E1
- <sup>(7)</sup> Outline conforms to JEDEC<sup>®</sup> TO-220, except D2

Revision: 13-Jun-2019

 $<sup>^{(1)}\,</sup>$  Dimensioning and tolerancing as per ASME Y14.5M-1994

<sup>(3)</sup> Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body



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